

# David J Smith

## List of Publications by Citations

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673  
papers

16,625  
citations

63  
h-index

99  
g-index

686  
ext. papers

17,520  
ext. citations

4.1  
avg, IF

6.36  
L-index

#	Paper	IF	Citations
673	Giant magnetoresistance in antiferromagnetic Co/Cu multilayers. <i>Applied Physics Letters</i> , <b>1991</b> , 58, 2710-2712	3.4	534
672	Bulk production of a new form of sp(2) carbon: crystalline graphene nanoribbons. <i>Nano Letters</i> , <b>2008</b> , 8, 2773-8	11.5	524
671	Covalently bonded three-dimensional carbon nanotube solids via boron induced nanojunctions. <i>Scientific Reports</i> , <b>2012</b> , 2, 363	4.9	300
670	An investigation of grain boundaries in submicrometer-grained Al-Mg solid solution alloys using high-resolution electron microscopy. <i>Journal of Materials Research</i> , <b>1996</b> , 11, 1880-1890	2.5	291
669	Direct surface imaging in small metal particles. <i>Nature</i> , <b>1983</b> , 303, 316-317	50.4	227
668	Ge <sub>1-x</sub> Sn <sub>x</sub> semiconductors for band-gap and lattice engineering. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 2992-2994	3.4	217
667	Nitrogen-mediated carbon nanotube growth: diameter reduction, metallicity, bundle dispersability, and bamboo-like structure formation. <i>ACS Nano</i> , <b>2007</b> , 1, 369-75	16.7	185
666	Observation of ferromagnetism above 900K in Cr <sub>0.5</sub> Ta <sub>0.5</sub> N and Cr <sub>0.5</sub> Al <sub>0.5</sub> N. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 4076-4078	3.4	182
665	Heterodoped nanotubes: theory, synthesis, and characterization of phosphorus-nitrogen doped multiwalled carbon nanotubes. <i>ACS Nano</i> , <b>2008</b> , 2, 441-8	16.7	165
664	Strain-Driven Alloying in Ge/Si(100) Coherent Islands. <i>Physical Review Letters</i> , <b>1999</b> , 83, 1199-1202	7.4	163
663	The importance of beam alignment and crystal tilt in high resolution electron microscopy. <i>Ultramicroscopy</i> , <b>1983</b> , 11, 263-281	3.1	161
662	High resolution studies of small particles of gold and silver. <i>Journal of Crystal Growth</i> , <b>1981</b> , 54, 425-432	1.6	160
661	Synthesis, characterization, and modeling of high quality ferromagnetic Cr-doped AlN thin films. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 3047-3049	3.4	159
660	Imaging of atomic clouds outside the surfaces of gold crystals by electron microscopy. <i>Nature</i> , <b>1985</b> , 317, 47-49	50.4	157
659	Atomic structure of symmetric tilt grain boundaries in NiO. <i>Physical Review Letters</i> , <b>1987</b> , 59, 2887-2890	7.4	155
658	Electron Holography: Phase Imaging with Nanometer Resolution. <i>Annual Review of Materials Research</i> , <b>2007</b> , 37, 729-767	12.8	152
657	Evolution of Ge/Si(100) islands: Island size and temperature dependence. <i>Journal of Applied Physics</i> , <b>2000</b> , 87, 2245-2254	2.5	143

656	Observations of grain boundary structure in submicrometer-grained Cu and Ni using high-resolution electron microscopy. <i>Journal of Materials Research</i> , <b>1998</b> , 13, 446-450	2.5	138
655	Formation of threading defects in GaN wurtzite films grown on nonisomorphic substrates. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 2063-2065	3.4	138
654	Accurate measurements of mean inner potential of crystal wedges using digital electron holograms. <i>Ultramicroscopy</i> , <b>1993</b> , 50, 285-299	3.1	137
653	Ultimate resolution in the electron microscope?. <i>Materials Today</i> , <b>2008</b> , 11, 30-38	21.8	128
652	Deep ultraviolet emitting AlGaIn quantum wells with high internal quantum efficiency. <i>Applied Physics Letters</i> , <b>2009</b> , 94, 181907	3.4	118
651	Direct observation of potential distribution across Si/Si p-n junctions using off-axis electron holography. <i>Applied Physics Letters</i> , <b>1994</b> , 65, 2603-2605	3.4	114
650	Endotaxial silicide nanowires. <i>Physical Review Letters</i> , <b>2004</b> , 93, 256102	7.4	111
649	The Study of Heterogeneous Catalysts by High-Resolution Transmission Electron Microscopy. <i>Catalysis Reviews - Science and Engineering</i> , <b>1992</b> , 34, 129-178	12.6	109
648	Chemical vapor deposition synthesis of N-, P-, and Si-doped single-walled carbon nanotubes. <i>ACS Nano</i> , <b>2010</b> , 4, 1696-702	16.7	101
647	Direct observation of the surfaces of small metal crystallites: rhodium supported on titania. <i>Langmuir</i> , <b>1988</b> , 4, 827-830	4	98
646	Structural properties of InN films grown on GaAs substrates: observation of the zincblende polytype. <i>Journal of Crystal Growth</i> , <b>1993</b> , 127, 204-208	1.6	97
645	Above 400-K robust perpendicular ferromagnetic phase in a topological insulator. <i>Science Advances</i> , <b>2017</b> , 3, e1700307	14.3	96
644	Optical properties of GaN grown on ZnO by reactive molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 467-469	3.4	91
643	Spin-dependent transport of CoBiO <sub>2</sub> granular films approaching percolation. <i>Physical Review B</i> , <b>2000</b> , 62, 14273-14278	3.3	90
642	Microstructure and optical properties of epitaxial GaN on ZnO (0001) grown by reactive molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>1998</b> , 83, 983-990	2.5	90
641	Reversibility of strong metal-support interactions on Rh/TiO <sub>2</sub> . <i>Journal of Catalysis</i> , <b>1989</b> , 118, 227-237	7.3	90
640	Mapping of electrostatic potential in deep submicron CMOS devices by electron holography. <i>Physical Review Letters</i> , <b>2002</b> , 89, 025502	7.4	89
639	Towards quantitative electron holography of magnetic thin films using in situ magnetization reversal. <i>Ultramicroscopy</i> , <b>1998</b> , 74, 61-73	3.1	85

638	Vapor-liquid-solid growth of germanium nanostructures on silicon. <i>Journal of Applied Physics</i> , <b>2004</b> , 96, 7556-7567	2.5	85
637	Magnetic interactions within patterned cobalt nanostructures using off-axis electron holography. <i>Journal of Applied Physics</i> , <b>1998</b> , 84, 374-378	2.5	85
636	Electron microscopy at 1-Å resolution by entropy maximization and likelihood ranking. <i>Nature</i> , <b>1992</b> , 355, 605-609	50.4	85
635	Finite size effects on the moment and ordering temperature in antiferromagnetic CoO layers. <i>Physical Review B</i> , <b>2003</b> , 67,	3.3	83
634	High resolution studies of small particles of gold and silver. <i>Journal of Crystal Growth</i> , <b>1981</b> , 54, 433-438	1.6	82
633	The realization of atomic resolution with the electron microscope. <i>Reports on Progress in Physics</i> , <b>1997</b> , 60, 1513-1580	14.4	81
632	Interface structures in beta-silicon carbide thin films. <i>Applied Physics Letters</i> , <b>1987</b> , 50, 203-205	3.4	80
631	The electron-beam-induced reduction of transition metal oxide surfaces to metallic lower oxides. <i>Ultramicroscopy</i> , <b>1987</b> , 23, 299-303	3.1	80
630	Direct atomic imaging of solid surfaces. <i>Ultramicroscopy</i> , <b>1985</b> , 16, 101-113	3.1	80
629	Simultaneous Enhancement of Electrical Conductivity and Thermopower of Bi <sub>2</sub> Te <sub>3</sub> by Multifunctionality of Native Defects. <i>Advanced Materials</i> , <b>2015</b> , 27, 3681-6	24	79
628	Orientation dependence of high speed silicon crystal growth from the melt. <i>Journal of Crystal Growth</i> , <b>1984</b> , 68, 624-638	1.6	79
627	Chemical vapor deposition of heteroepitaxial Si <sub>1-x</sub> Ge <sub>x</sub> Cy films on (100)Si substrates. <i>Applied Physics Letters</i> , <b>1994</b> , 65, 2559-2561	3.4	78
626	Characterization of structural defects in wurtzite GaN grown on 6H SiC using plasma-enhanced molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 1830-1832	3.4	77
625	HREM and STEM of defects in multiply-twinned particles. <i>Journal of Microscopy</i> , <b>1983</b> , 130, 249-261	1.9	76
624	Enhancing exchange bias with diluted antiferromagnets. <i>Physical Review Letters</i> , <b>2006</b> , 96, 117204	7.4	75
623	Atomic-resolution study of structural rearrangements in small platinum crystals. <i>Ultramicroscopy</i> , <b>1986</b> , 20, 71-75	3.1	75
622	Epitaxial lateral overgrowth of (112̄) semipolar GaN on (1100) m-plane sapphire by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 182109	3.4	74
621	Nanometer-scale composition measurements of Ge/Si(100) islands. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 1473-1475	3.4	74

620	Formation of a Tetrameric, Cyclooctane-like, Azidochlorogallane, $[\text{HClGaN}_3]_4$ , and Related Azidogallanes. Exothermic Single-Source Precursors to GaN Nanostructures. <i>Journal of the American Chemical Society</i> , <b>1998</b> , 120, 5233-5237	16.4	73
619	Characterization of Al(Cr)N and Ga(Cr)N dilute magnetic semiconductors. <i>Journal of Magnetism and Magnetic Materials</i> , <b>2005</b> , 290-291, 1395-1397	2.8	72
618	Quantitative analysis of one-dimensional dopant profile by electron holography. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 3213-3215	3.4	71
617	An atomistic branching mechanism for carbon nanotubes: sulfur as the triggering agent. <i>Angewandte Chemie - International Edition</i> , <b>2008</b> , 47, 2948-53	16.4	69
616	Magnetic iron silicide nanowires on Si(110). <i>Applied Physics Letters</i> , <b>2006</b> , 88, 113111	3.4	66
615	Magnetic correlations in non-percolated $\text{Co}_5\text{BiO}_2$ granular films. <i>Journal of Magnetism and Magnetic Materials</i> , <b>2000</b> , 221, 1-9	2.8	66
614	Magnetic anisotropy and microstructure in molecular beam epitaxial FePt (110)/MgO (110). <i>Journal of Applied Physics</i> , <b>1998</b> , 84, 934-939	2.5	66
613	Procedures for focusing, stigmating and alignment in high resolution electron microscopy. <i>Journal of Microscopy</i> , <b>1983</b> , 130, 187-201	1.9	65
612	Carrier density modulation in a germanium heterostructure by ferroelectric switching. <i>Nature Communications</i> , <b>2015</b> , 6, 6067	17.4	64
611	High quality large-area CdTe(211)B on Si(211) grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>1997</b> , 71, 1810-1812	3.4	63
610	Correlation of coercivity and microstructure of thin CoFe films. <i>Journal of Applied Physics</i> , <b>2000</b> , 88, 2058-2062	2.9	63
609	Atomic resolution electron microscopy of NiO grain boundaries. <i>Ultramicroscopy</i> , <b>1987</b> , 22, 57-70	3.1	62
608	Direct atomic imaging of solid surfaces. <i>Surface Science</i> , <b>1984</b> , 143, 495-508	1.8	61
607	Grain boundary structure in AlMg and AlMgBc alloys after equal-channel angular pressing. <i>Journal of Materials Research</i> , <b>2001</b> , 16, 583-589	2.5	60
606	Direct Observation of Elastic and Plastic Deformations at Au(111) Surfaces. <i>Physical Review Letters</i> , <b>1984</b> , 52, 656-658	7.4	60
605	Observation of vertical honeycomb structure in InAlN/GaN heterostructures due to lateral phase separation. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 081917	3.4	58
604	Switching asymmetries in closely coupled magnetic nanostructure arrays. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 2641-2643	3.4	58
603	Atomic-scale chemical imaging and quantification of metallic alloy structures by energy-dispersive X-ray spectroscopy. <i>Scientific Reports</i> , <b>2014</b> , 4, 3945	4.9	57

602	Growth and characterization of pseudomorphic single crystal zinc blende MnS. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 2690-2692	3-4	57
601	The determination of atomic positions in high-resolution electron micrographs. <i>Ultramicroscopy</i> , <b>1985</b> , 18, 39-47	3-1	57
600	Electron-beam-induced reactions at transition-metal oxide surfaces. <i>Vacuum</i> , <b>1991</b> , 42, 301-308	3-7	56
599	Characterization of Group III-nitride semiconductors by high-resolution electron microscopy. <i>Journal of Crystal Growth</i> , <b>1995</b> , 152, 135-142	1.6	55
598	Production and characterization of a monoclonal antibody against the beta-adrenergic agonist ractopamine. <i>Journal of Agricultural and Food Chemistry</i> , <b>2000</b> , 48, 4020-6	5-7	54
597	Microstructure of heteroepitaxial CdTe grown on misoriented Si(001) substrates. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 1591-1593	3-4	54
596	Development of aberration-corrected electron microscopy. <i>Microscopy and Microanalysis</i> , <b>2008</b> , 14, 2-15	0.5	53
595	Methods for the measurement of rigid-body displacements at edge-on boundaries using high-resolution electron microscopy. <i>Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties</i> , <b>1985</b> , 50, 375-391		53
594	Plastic Deformation of BaTiO <sub>3</sub> Ceramics by High-pressure Torsion and Changes in Phase Transformations, Optical and Dielectric Properties. <i>Materials Research Letters</i> , <b>2015</b> , 3, 216-221	7-4	52
593	Effectiveness of TiN porous templates on the reduction of threading dislocations in GaN overgrowth by organometallic vapor-phase epitaxy. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 043108	3-4	52
592	Dynamic observation of defect annealing in CdTe at lattice resolution. <i>Nature</i> , <b>1982</b> , 298, 127-131	50-4	52
591	Dysprosium silicide nanowires on Si(110). <i>Applied Physics Letters</i> , <b>2003</b> , 83, 5292-5294	3-4	51
590	Origin of magnetization decay in spin-dependent tunnel junctions. <i>Science</i> , <b>1999</b> , 286, 1337-40	33-3	50
589	Structural properties of GaN films grown on sapphire by molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 1141-1143	3-4	50
588	Endotaxial silicide nanowires: A review. <i>Thin Solid Films</i> , <b>2011</b> , 519, 8434-8440	2.2	49
587	Atomic imaging of oxide surfaces. <i>Surface Science</i> , <b>1986</b> , 175, 673-683	1.8	49
586	Sub-250 nm room-temperature optical gain from AlGaIn/AlN multiple quantum wells with strong band-structure potential fluctuations. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 061111	3-4	48
585	Tunable band structure in diamond-cubic tin-germanium alloys grown on silicon substrates. <i>Solid State Communications</i> , <b>2003</b> , 127, 355-359	1.6	48

584	Optimisation and applications of the Cambridge University 600 kV high resolution electron microscope. <i>Ultramicroscopy</i> , <b>1982</b> , 9, 203-213	3.1	48
583	Annealing of CoFeB/MgO based single and double barrier magnetic tunnel junctions: Tunnel magnetoresistance, bias dependence, and output voltage. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 033916	2.5	47
582	Non-anomalous high-resolution imaging of crystalline materials. <i>Ultramicroscopy</i> , <b>1985</b> , 16, 19-31	3.1	47
581	Magnetic tunnel junctions thermally stable to above 300 °C. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 543-545	3.4	46
580	The measurement of boundary displacements in metals. <i>Ultramicroscopy</i> , <b>1984</b> , 14, 145-154	3.1	46
579	Epitaxial titanium silicide islands and nanowires. <i>Surface Science</i> , <b>2003</b> , 524, 148-156	1.8	45
578	Studies of electron irradiation and annealing effects on TiO <sub>2</sub> surfaces in ultrahigh vacuum using high-resolution electron microscopy. <i>Surface Science</i> , <b>1991</b> , 250, 169-178	1.8	45
577	The high resolution electron microscopy of stacking defects in Cu <sub>31</sub> Ni <sub>69</sub> shape memory alloy. <i>Journal of Microscopy</i> , <b>1983</b> , 129, 295-306	1.9	45
576	The Role of Sulfur in the Synthesis of Novel Carbon Morphologies: From Covalent Y-Junctions to Sea-Urchin-Like Structures. <i>Advanced Functional Materials</i> , <b>2009</b> , 19, 1193-1199	15.6	44
575	Off-axis electron holography of epitaxial FePt films. <i>Journal of Applied Physics</i> , <b>1997</b> , 82, 2461-2465	2.5	44
574	Mapping In concentration, strain, and internal electric field in InGaN/GaN quantum well structure. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 2103-2105	3.4	44
573	Observations of nanocrystals in thin TbFeCo films. <i>Applied Physics Letters</i> , <b>1989</b> , 55, 919-921	3.4	44
572	Observation of hole accumulation in Ge/Si core/shell nanowires using off-axis electron holography. <i>Nano Letters</i> , <b>2011</b> , 11, 493-7	11.5	43
571	Oriented growth of single-crystal Ni nanowires onto amorphous SiO <sub>2</sub> . <i>Nano Letters</i> , <b>2010</b> , 10, 5070-5	11.5	43
570	Fabrication and thermal stability of a nanocrystalline Ni <sub>40</sub> Cr alloy: Comparison with pure Cu and Ni. <i>Journal of Materials Research</i> , <b>1999</b> , 14, 4200-4207	2.5	43
569	Synthesis and characterization of heteroepitaxial diamond-structured Ge <sub>1-x</sub> C <sub>x</sub> (x=1.5B.0%) alloys using chemical vapor deposition. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 2407-2409	3.4	43
568	Atomic resolution with a 600-kV electron microscope. <i>Nature</i> , <b>1979</b> , 281, 49-51	50.4	43
567	Quantitative phase imaging of nanoscale electrostatic and magnetic fields using off-axis electron holography. <i>Ultramicroscopy</i> , <b>2010</b> , 110, 375-382	3.1	42

- 566 Simple chemical routes to diamond-cubic germanium in alloys. *Applied Physics Letters*, **2001**, 78, 3607-3609 42
- 565 Dependence of giant magnetoresistance on Cu-layer thickness in Co/Cu multilayers: A simple dilution effect. *Physical Review B*, **1993**, 47, 9136-9139 3.3 42
- 564 Direct observation of the structure of a metallic alloy glass. *Nature*, **1979**, 281, 465-467 50.4 42
- 563 Effect of microstructure on magnetic properties and anisotropy distributions in Co/Pd thin films and nanostructures. *Physical Review B*, **2009**, 80, 3.3 41
- 562 Measurement of lattice-fringe vectors from digital HREM images: experimental precision. *Ultramicroscopy*, **1995**, 57, 409-422 3.1 41
- 561 Atomic and electronic structure of the ferroelectric BaTiO<sub>3</sub>/Ge(001) interface. *Applied Physics Letters*, **2014**, 104, 242908 3.4 40
- 560 Atomic layer deposition of crystalline SrHfO<sub>3</sub> directly on Ge (001) for high-k dielectric applications. *Journal of Applied Physics*, **2015**, 117, 054101 2.5 39
- 559 Defect characterization for epitaxial HgCdTe alloys by electron microscopy. *Journal of Crystal Growth*, **2004**, 265, 224-234 1.6 39
- 558 Influence of interface alloying on the magnetic properties of Co/Pd multilayers. *Applied Physics Letters*, **2003**, 83, 5259-5261 3.4 39
- 557 Interaction of small and extended defects in nonstoichiometric oxides. *Nature*, **1984**, 309, 319-321 50.4 39
- 556 A Chemical Route to Monolithic Integration of Crystalline Oxides on Semiconductors. *Advanced Materials Interfaces*, **2014**, 1, 1400081 4.6 38
- 555 Epitaxial strontium titanate films grown by atomic layer deposition on SrTiO<sub>3</sub>-buffered Si(001) substrates. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2013**, 31, 01A136 2.9 38
- 554 Spin-dependent tunneling in discontinuous CoBiO<sub>2</sub> magnetic tunnel junctions. *Applied Physics Letters*, **1998**, 73, 535-537 3.4 38
- 553 Quenched magnetic moment in Mn-doped amorphous Si films. *Physical Review B*, **2008**, 77, 3.3 37
- 552 Hollow metallic microspheres produced by spark erosion. *Applied Physics Letters*, **2004**, 85, 940-942 3.4 37
- 551 Growth and characterization of CdTe/Si heterostructures [Effect of substrate orientation. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2000**, 77, 93-100 3.1 36
- 550 The oxidation of small rhodium metal particles. *Ultramicroscopy*, **1989**, 31, 132-137 3.1 36
- 549 A systematic analysis of HREM imaging of sphalerite semiconductors. *Ultramicroscopy*, **1989**, 27, 131-150.1 36

548	Structure and orientation of epitaxial titanium silicide nanowires determined by electron microdiffraction. <i>Journal of Applied Physics</i> , <b>2003</b> , 93, 5670-5674	2.5	35
547	The role of Cr substitution on the ferromagnetic properties of Ga <sub>1-x</sub> Cr <sub>x</sub> N. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 012504	3-4	35
546	Development of a low-temperature GaN chemical vapor deposition process based on a single molecular source H <sub>2</sub> GaN <sub>3</sub> . <i>Applied Physics Letters</i> , <b>1999</b> , 74, 883-885	3-4	35
545	Real-Time Atomic-Resolution Imaging of Polymorphic Changes in Ruthenium Clusters. <i>Angewandte Chemie International Edition in English</i> , <b>1988</b> , 27, 555-558		35
544	Metallisation of oxide surfaces observed by in situ high-resolution electron microscopy. <i>Ultramicroscopy</i> , <b>1985</b> , 17, 387-391	3-1	35
543	Direct lattice imaging of small metal particles. <i>Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties</i> , <b>1981</b> , 44, 735-740		35
542	Evaluation of antimony segregation in InAs/InAs <sub>1-x</sub> Sb <sub>x</sub> type-II superlattices grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>2016</b> , 119, 095702	2.5	35
541	Quasi-two-dimensional electron gas at the epitaxial alumina/SrTiO <sub>3</sub> interface: Control of oxygen vacancies. <i>Journal of Applied Physics</i> , <b>2015</b> , 117, 095303	2.5	34
540	Reliability studies of AlGaIn/GaN high electron mobility transistors. <i>Semiconductor Science and Technology</i> , <b>2013</b> , 28, 074019	1.8	34
539	Intersubband absorption in AlN/GaN/AlGaIn coupled quantum wells. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 141104	3-4	34
538	Complex and incommensurate ordering in Al <sub>0.72</sub> Ga <sub>0.28</sub> N thin films grown by plasma-assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 181915	3-4	34
537	Molecular beam epitaxy of InAlN/GaN heterostructures for high electron mobility transistors. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>2005</b> , 23, 1204		34
536	Influence of 6H-SiC(0001) substrate surface morphology on the growth of AlN epitaxial layers. <i>Applied Physics Letters</i> , <b>1999</b> , 74, 985-987	3-4	34
535	A theoretical analysis of HREM imaging for <110> tetrahedral semiconductors. <i>Ultramicroscopy</i> , <b>1989</b> , 27, 19-34	3-1	34
534	Atom hopping on small gold particles imaged by high-resolution electron microscopy. <i>Die Naturwissenschaften</i> , <b>1985</b> , 72, 539-541	2	34
533	Electric-Field-Driven Degradation in off-State Step-Stressed AlGaIn/GaN High-Electron Mobility Transistors. <i>IEEE Transactions on Device and Materials Reliability</i> , <b>2011</b> , 11, 187-193	1.6	33
532	Microstructural evolution of Ge/Si(1 0 0) nanoscale islands. <i>Journal of Crystal Growth</i> , <b>2003</b> , 259, 232-244	1.6	33
531	Semiconductor dopant profiling by off-axis electron holography. <i>Ultramicroscopy</i> , <b>2003</b> , 94, 149-61	3-1	33

530	Low-threshold continuous-wave operation of quantum-cascade lasers grown by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 5842-5844	3.4	32
529	Magnetically soft, high-moment, high-resistivity thin films using discontinuous metal/native oxide multilayers. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 224-226	3.4	32
528	Determination of mean inner potential of germanium using off-axis electron holography. <i>Acta Crystallographica Section A: Foundations and Advances</i> , <b>1999</b> , 55, 652-658		32
527	Dependence of giant magnetoresistance on grain size in Co/Cu multilayers. <i>Physical Review B</i> , <b>1994</b> , 50, 4232-4235	3.3	32
526	Applications of electron holography to the study of interfaces. <i>Ultramicroscopy</i> , <b>1993</b> , 50, 301-311	3.1	32
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524	Direct Mapping of Charge Distribution during Lithiation of Ge Nanowires Using Off-Axis Electron Holography. <i>Nano Letters</i> , <b>2016</b> , 16, 3748-53	11.5	31
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